

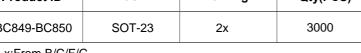
#### **Features**

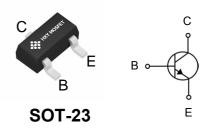
Collector Current: I<sub>C</sub>= 0.1A

Power Dissipation of 250mW

## **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)	
BC849-BC850	SOT-23	2x	3000	





x:From B/C/F/G

## Maxmim Ratings (Ta=25 unless otherwise noted)

Symbl	Parameter	Value	Unit	
VCBO	Collector-Base Voltage	9	30	V
VCBO	BC85	0	50	V
VCEO	Collector-Emitter Voltage BC849	9	30	
		0	45	V
VEBO	Emitter-Base Voltage		5	V
Ic	Collector Current-Continuous		01	Α
T <sub>j</sub>	Junction Temperature		150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature		-55-150	°C

#### Classifiction Of hFE

Rank	BC849B	BC849C	BC850B	BC850C
Marking	2B	2C	2F	2G



## Electrcal Charcteristics (Ta=25 unless otherwise specified)

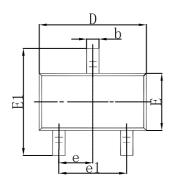
Parameter		Symbol	Testconditons	Min	Тур	Max	Unit
collector cut-off current		Ісво	IE = 0; VCB = 30 V			15	nA
			IE = 0; VCB = 30 V; Tj = 150 °C			5	ìΑ
emitter cut-off curr	ent	ІЕВО	IC = 0; VEB = 5 V			100	nA
DC current gain BC849B; BC850B			In 403 A. Von 516		240		
	BC849C; BC850C	hfe	Ic = 10 i A; VcE = 5 V;		450		
DC current gain	BC849B; BC850B	TIFE			290	450	
	BC849C; BC850C		Ic = 2  mA; $VcE = 5  V$ ;	420	520	800	
collector-emitter saturation voltage		VCEsat	Ic = 10 mA; IB = 0.5 mA		90	250	mV
			Ic = 100 mA; IB = 5 mA		200	600	mV
base-emitter saturation voltage		VBEsat	Ic = 10 mA; IB = 0.5 mA; *1		700		mV
			Ic = 100 mA; IB = 5 mA; *1		900		mV
base-emitter voltage		VBE	Ic = 2 mA; VcE = 5 V; *2	580	660	700	mV
			Ic = 10 mA; VcE = 5 V;*2			770	mV
collector capacitance Cc IE		IE = ie = 0; VCB = 10 V; f = 1 MHz		2.5		pF	
emitter capacitanc	mitter capacitance Ce Ic = ic = 0		Ic = ic = 0; VEB = 500 mV; f = 1 MHz		11		pF
transition frequency		fT	Ic = 10 mA; VcE = 5 V; f = 100 MHz	100			MHz
noise figure		F	Ic = 200 ìA; V cE = 5 V; Rs = 2 kÙ,f = 10 Hz to 15.7 kHz			4	dB
			Ic = 200 iA; V cE = 5 V; Rs = 2 k $\dot{U}$ ,f = 1 kHz; B = 200 Hz			4	dB

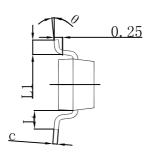
<sup>\*1</sup> VBEsat decreases by about 1.7 mV/K with increasing temperature.

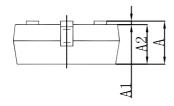
<sup>\*2</sup> VBE decreases by about 2 mV/K with increasing temperature.

# **Package Dimensions**

SOT-23

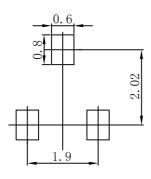






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **Suggested Pad Layout**



- Note:
  1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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